

# FDT434P

# P-Channel 2.5V Specified PowerTrench® MOSFET

### **General Description**

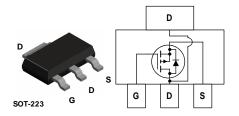
This P-Channel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

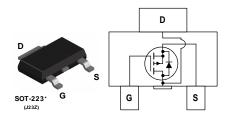
### **Applications**

- Low Dropout Regulator
- DC/DC converter
- · Load switch
- Motor driving

#### **Features**

- -5.5 A, -20 V.  $R_{DS(ON)} = 0.050 \Omega$  @  $V_{GS} = -4.5 \text{ V}$  $R_{DS(ON)} = 0.070 \Omega$  @  $V_{GS} = -2.5 \text{ V}$ .
- Low gate charge (13nC typical)
- High performance trench technology for extremely low  $R_{\mbox{\scriptsize DS(ON)}}$  .
- High power and current handling capability in a widely used surface mount package.





### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		-20	V
V <sub>GSS</sub>	Gate-Source Voltage		±8	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	-6	Α
	- Pulsed		-30	
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1a)	3	W
		(Note 1b)	1.3	
		(Note 1c)	1.1	
$T_J$ , $T_{stg}$	Operating and Storage Junction Temperat	ture Range	-55 to +150	°C

### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	42	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	12	°C/W

Package Marking and Ordering Information

-	Device Marking	Device	Reel Size	Tape width	Quantity	
-	434	FDT434P	13"	12mm	2500 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			I	I	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$ , Referenced to $25^{\circ}C$		-28		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V},  V_{GS} = 0 \text{ V}$			-1	μΑ
I <sub>GSSF</sub>	Gate–Body Leakage Current, Forward	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
$I_{GSSR}$	Gate–Body Leakage Current, Reverse	$V_{GS} = -8 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-0.6	-1	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$ , Referenced to $25^{\circ}C$		2		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V},  I_D = -6 \text{ A}$ $V_{GS} = -4.5 \text{ V},  I_D = -6 \text{ A}$ $T_{J} = 125^{\circ}\text{C}$		0.040 0.067	0.050 0.083	Ω
		$V_{GS} = -2.5 \text{ V},  I_D = -4 \text{ A}$ $V_{GS} = -4.5 \text{ V},  V_{DS} = -5 \text{ V}$		0.050	0.070	
I <sub>D(on)</sub>	On–State Drain Current		-20			Α
<b>G</b> FS	Forward Transconductance	$V_{DS} = -10 \text{ V}, \qquad I_D = -6 \text{ A}$		6.5		S
Dynamic	Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -10 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		1240		pF
Coss	Output Capacitance	f = 1.0 MHz		270		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			100		pF
Switchin	g Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = -5 \text{ V}, \qquad I_D = -1 \text{ A},$		8	16	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, \qquad R_{GEN} = 6 \Omega$		15	25	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	7		45	65	ns
t <sub>f</sub>	Turn-Off Fall Time	7		30	50	ns
Qg	Total Gate Charge	$V_{DS} = -10 \text{ V}, \qquad I_{D} = -6 \text{ A},$		13	19	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$		1.8		nC
$Q_{gd}$	Gate-Drain Charge			3		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings		•	•	
I <sub>S</sub>	Maximum Continuous Drain–Source				-1.3	Α
V <sub>SD</sub>	Drain-Source Diode Forward	$V_{GS} = 0 \text{ V},  I_S = -2.1 \text{ A}  \text{(Note 2)}$		-0.75	-1.2	V

### Notes:

<sup>1.</sup>  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a) 42°C/W when mounted on a 1in² pad of 2 oz copper



b) 95°/W when mounted on a .0066 in² pad of 2 oz copper

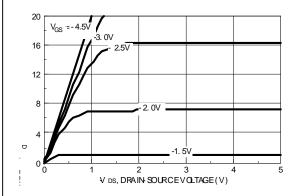


c) 110°/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width <  $300\mu s$ , Duty Cycle < 2.0%

# **Typical Characteristics**



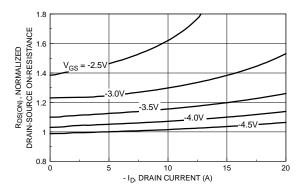
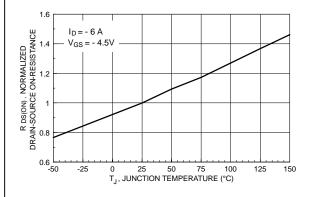


Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



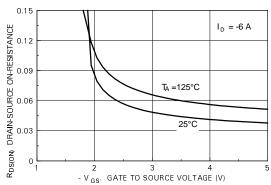
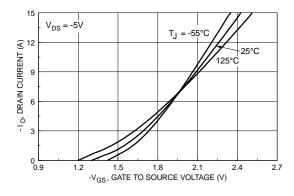


Figure 3. On-Resistance Variation withTemperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



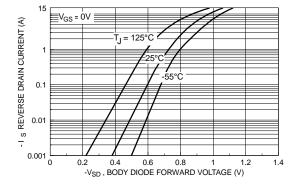
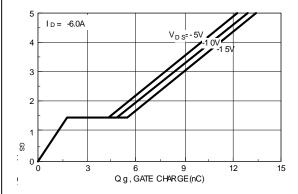


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# **Typical Characteristics**



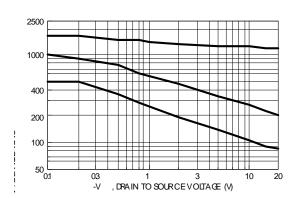


Figure 7. Gate Charge Characteristics.

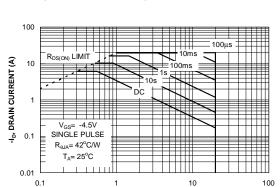


Figure 8. Capacitance Characteristics.

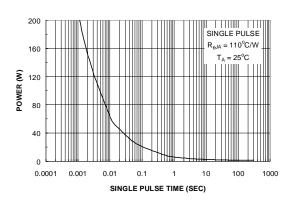


Figure 9. Maximum Safe Operating Area.

-V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)



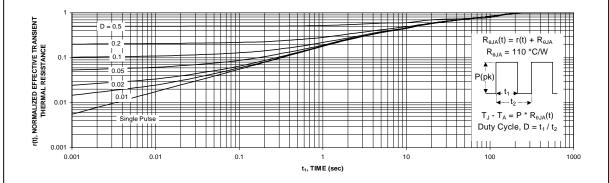


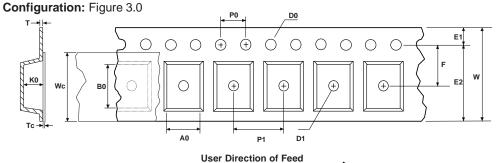
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient themal response will change depending on the circuit board design.





### **SOT-223 Embossed Carrier Tape**

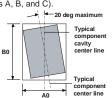


Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
<b>SOT-223</b> (12mm)	6.83 +/-0.10	7.42 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.88 +/-0.10	0.292 +/- 0.0130	9.5 +/-0.025	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

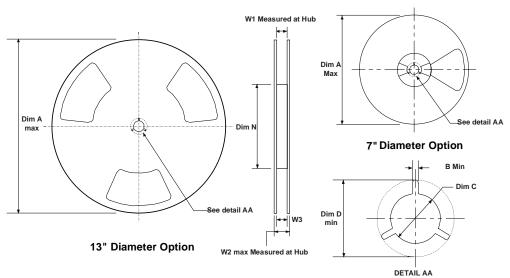


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

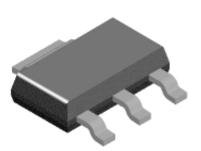
### SOT-223 Reel Configuration: Figure 4.0

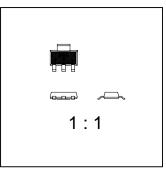


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

# SOT-223 Tape and Reel Data and Package Dimensions, continued

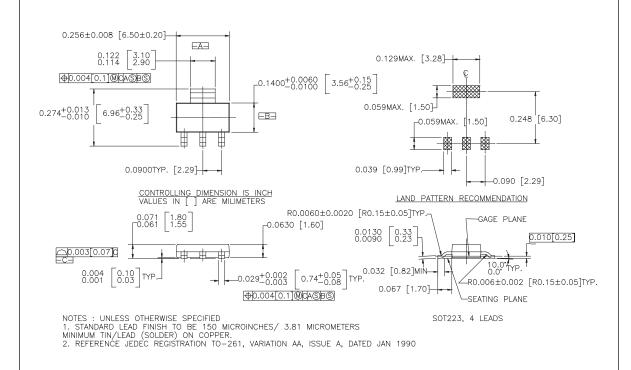
# SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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